

Phenitec Original NPN Bipolar Transistor Characteristics Table

New = New device

*= typical, \$=VCER, #=VCES

フェニテックセミコンダクター株式会社

Chip	VCBO (V)	VCEO (V)	VEBO (V)	IC (A)	hFE (-)	hFE		VCE(sat)			fT (MHz)	fT		Cob (pF)	Complement		Comment
						VCE(V)	IC(A)	(V)	IC(A)	IB(A)		VCE(V)	IE(A)		VCB(V)	Product	
CP020	400	350	7	0.1	30-333	10	10m	0.5	0.1	10m	100*	30	10m	-	-	AP020	High Voltage Driver
C5038	30	25	3	50m	110-	10	4m	0.5	4m	0.4m	650	10	4m	0.7	10	-	Radio Frequency
CP041	120	120	5	50m	180-560	6	2m	0.5	50m	5m	140*	12	2m	3.2*	12	-	Low VCE(sat)
CP081	60	30	5	0.5	100-300	10	0.15	1.6	0.5	50m	250	20	20m	8	10	-	Low VCE(sat)
CP082	60	40	6	0.2	90-333	1	10m	0.3	50m	5m	250	20	10m	4	5	-	Low VCE(sat)
C5333	60	50	5	0.2	63-	6	1m	0.3	0.1	10m	130*	12	2m	3.5	12	A5335	Low VCE(sat)
C5334	80	65	6	0.1	110-450	5	2m	0.6	0.1	5m	-	-	-	-	-	-	Low VCE(sat)
CP370	40	15	4.5	0.2	-120	1	10m	0.5	0.1	10m	-	-	-	4	5	-	High Speed Switching
CP380	35	30	4	50m	36-265	12	2m	0.4	10m	1m	100	10	1m	3.2	10	-	Low VCE(sat)
New CP841	300	300	5	0.5	80-300	10	0.1	0.3	0.25	25m	75	10	30m	5	10	-	High Voltage Driver
New C5843	140	80	7	1	100-300	10	0.15	0.5	0.5	50m	100	10	50m	12	10	-	Low VCE(sat)
C5862	40	40	5	2	350-680	2	0.1	0.18	1	50m	100	10	0.1	20	10	A5862	Very Low VCE(sat)
C5863	120	100	5	2	100-300	2	0.5	0.5	1	0.1	140	5	0.1	30	10	A5863	Very Low VCE(sat)
C5866	40	40	5	2	350-680	2	0.1	0.18	1	50m	100	10	0.1	20	10	A5866	Very Low VCE(sat)
CP869	600	400	7	0.3	100-200	10	20m	0.5	50m	5m	50	10	20m	7	20	-	High Voltage Driver
CP872	350	300	7	50m	64-310	10	10m	0.5	10m	1m	56*	10	10m	1.3*	20	AP872	High Voltage Driver
C5877	50	25	7	5	250-550	2	0.5	0.5	4	0.2	400*	10	0.5	15*	10	-	Low VCE(sat)
CP879	1600	800	6	1	20-40	5	10m	0.3	0.2	40m	-	-	-	-	-	-	High Voltage Switching
CP880	1600	800	6	0.3	20-40	5	10m	0.3	50m	10m	-	-	-	-	-	-	High Voltage Switching
CP884	500	500	5	0.15	150-300	10	1m	0.5	50m	10m	50*	20	10m	8	20	AP884	High Voltage Driver
C5886	40	40	6	5	300-	2	0.5	0.15	2	0.2	70	10	0.1	75	10	A5886	Very Low VCE(sat)
C5887	60	50	5	0.1	120-400	6	2m	0.25	0.1	10m	60	10	1m	1.4*	10	A5887	Low VCE(sat)
C5893	40	40	5	1	300-900	5	0.5	0.5	1	0.1	150	10	50m	10	10	A5893	Very Low VCE(sat)
C5894	100	100	6	5	60-240	2	2	1	5	0.5	90*	10	0.1	80	50	-	Low VCE(sat)
C5895	50	50	5	3	300-700	2	1	0.37	3	0.3	100	5	0.1	25	10	A5895	Very Low VCE(sat)
CP896	400	400	5	0.5	50-	5	0.1	0.5	0.1	10m	50	20	20m	10	20	-	High Voltage Driver
CP898	60	40	8	0.6	100-300	1	0.15	0.4	0.15	15m	250	10	20m	6.5	5	-	High Speed Switching
CP899	75	40	6	0.6	100-300	10	0.15	1	0.5	50m	300	20	20m	8	10	-	High Speed Switching
C5901	80	60	5	1	100-	5	1	0.28	1	0.1	150	10	50m	10	10	A5901	Very Low VCE(sat)
C5902	60	60	7	5	200-400	1	2	0.3	2	0.2	70*	10	50m	70	10	-	Very Low VCE(sat)
C5904	80	60	5	3	100-300	2	0.5	0.6	3	0.3	140	5	0.1	30	10	-	Low VCE(sat)

Phenitec Original NPN Bipolar Transistor Characteristics Table

New = New device

*= typical, \$=VCER, #=VCES

フェニテックセミコンダクター株式会社

Chip	VCBO (V)	VCEO (V)	VEBO (V)	IC (A)	hFE (-)	VCE(sat)		VCE(sat) (V)	IC(A)	IB(A)	fT (MHz)	fT		Cob (pF)	Complement		Comment
						VCE(V)	IC(A)					VCE(V)	IE(A)		VCB(V)	Product	
C5906	200	170	6	5	40-	5	2	1	5	0.5	90*	10	0.1	80	50	-	Low VCE(sat)
C5908	20	20	5	5	500-	2	0.1	0.45	3	20m	150	5	50m	22*	10	A5908	Very Low VCE(sat)
C5909	12	12	5	4	500-	2	0.1	0.4	4	50m	150	5	50m	40*	10	A5909	Very Low VCE(sat)
C5910	50	50	5	2	200-	2	1	0.22	2	50m	100	10	50m	20	10	-	Very Low VCE(sat)
C5912	60	50	6	2	120-400	2	0.5	0.35	1	50m	280*	2	0.5	12*	10	-	Low VCE(sat)
C5913	100	50	7	3	400-1000	2	0.3	0.14	1	20m	250*	2	0.3	13*	10	A5914	Very Low VCE(sat)
C5915	40	20	7	4	400-1000	2	0.5	0.15	1.6	32m	200*	2	0.5	18*	10	A5889	Very Low VCE(sat)
C5917	300	200	7	2	190-450	5	0.1	0.18	1	50m	90*	10	0.1	16*	10	-	Low VCE(sat)
C5919	15	15	5	6	250-	2	0.5	0.3	3	60m	250*	2	0.5	33*	10	-	Very Low VCE(sat)
C5926	40	32	5	2	82-390	3	0.5	0.8	2	0.2	270*	5	50m	14*	10	A5926	Low VCE(sat)
C5932	300	200	6	1	140-340	5	0.2	0.25	0.5	25m	20	5	0.2	20	10	-	Low VCE(sat)
C5937	250	200	6	3	40-160	5	0.5	0.2	0.5	50m	50	10	0.1	30	10	-	Low VCE(sat)
CP938X	600	400	9	1	80-	10	0.25	1	1	0.25	-	-	-	-	-	-	High Voltage Driver
CP938	700	400	9	1	8-35	2	0.5	1	1	0.25	-	-	-	-	-	-	High Voltage Switching
C5942	80	50	6	3	180-610	2	0.1	0.3	2	50m	230*	5	50m	25*	10	(A5861)	Low VCE(sat)
C5946	80	50	6	5	200-560	2	0.5	0.24	2	0.1	400*	10	0.5	15*	10	-	Low VCE(sat)
C5949	170	60	6	3	160-440	2	0.1	0.35	2	50m	200*	5	50m	20*	10	-	Low VCE(sat)
C5951	180	160	5	1.5	80-360	5	0.15	1	0.5	50m	200*	5	0.15	13*	10	A5951	Low VCE(sat)
C5953	180	160	6	0.6	72-330	5	10m	0.2	50m	5m	100-300	10	10m	6	10	A5983	Low VCE(sat)
C5955	120	100	6	1	140-330	2	0.15	0.5	0.5	50m	100	5	50m	10	10	A5955	Low VCE(sat)
CP956	500	400	7	0.3	100-200	10	20m	0.5	50m	5m	50	10	20m	7	20	AP964	High Voltage Driver
CP958	400	400	6	0.3	80-300	10	10m	0.75	50m	5m	50	10	10m	2.5*	20	AP958	High Voltage Driver
CP963	60	40	6	0.2	100-300	1	10m	0.3	50m	5m	300	20	10m	4	5	AP963	High Speed Switching
CP964	500	400	7	0.3	60-200	10	20m	0.5	50m	5m	50	10	20m	7	20	AP964	High Voltage Driver
C5965	160	140	5	1	100-300	10	0.15	0.7	0.15	15m	100	10	50m	15	10	-	Low VCE(sat)
CP971	300	300	7	0.3	60-280	10	10m	0.5	0.1	10m	80*	10	10m	2.5*	20	AP971	High Voltage Driver
C5979	50	50	5	0.5	68-330	3	10m	0.5	0.15	15m	280*	5	50m	12	10	A5977	Low VCE(sat)
CP981	60	40	6	0.2	90-333	1	10m	0.3	50m	5m	250	20	10m	4	5	AP981	High Speed Switching
C5983	180	160	6	0.6	72-330	5	10m	0.2	50m	5m	100-300	10	10m	6	10	A5983	Low VCE(sat)
CP984	500	400	8	0.5	10-30	10	5m	0.4	50m	10m	10	10	10m	-	-	-	High Voltage Switching
C5985	80	60	5	1	130-300	5	0.5	0.5	1	0.1	150	10	50m	10	10	A5985	Low VCE(sat)

Phenitec Original NPN Bipolar Transistor Characteristics Table

New = New device

*= typical, \$=VCER, #=VCES

フェニテックセミコンダクター株式会社

Chip	VCBO (V)	VCEO (V)	VEBO (V)	IC (A)	hFE (-)	VCE(sat)		VCE(sat)			fT (MHz)	fT		Cob (pF)	Complement		Comment
						VCE(V)	IC(A)	(V)	IC(A)	IB(A)		VCE(V)	IE(A)		VCB(V)	Product	
C5987	200	100	6	6	120-300	2	2	0.4	5	0.25	190*	10	0.1	38*	10	A5987	Low VCE(sat)
C5988	150	60	6	6	120-300	1	2	0.55	6	0.3	150*	10	0.1	50*	10	A5988	Low VCE(sat)
C5991	30	18	3	50m	56-270	10	10m	0.5	20m	4m	1500*	10	10m	1.5	10	-	Radio Frequency
C5993	20	11	3	50m	56-180	10	5m	0.5	10m	5m	3200*	10	10m	1.5	10	-	Radio Frequency
CP998	60	40	6	0.6	100-300	10	0.15	1	0.5	50m	250	20	20m	8	10	-	High Speed Switching
CP999	400	400	7	0.3	50-150	10	20m	0.5	0.1	10m	50	10	20m	3*	20	-	High Voltage Driver
PR105	15	6	1.5	50m	50-250	5	10m	-	-	-	8000*	5	10m	1*	5	-	Radio Frequency
DP005	80	80	4	0.5	90-	1	10m	0.33	0.1	10m	115*	2	10m	4.5*	10	BP005	Low VCE(sat)
DP006	80	80	4	0.5	90-	1	10m	0.33	0.1	10m	-	-	-	-	-	-	Low VCE(sat)
DP010	40	32	5	0.5	82-390	3	10m	0.4	0.1	10m	250*	5	20m	6.2*	10	BP010	Low VCE(sat)
D5016	50	45	5	0.5	100-600	1	0.1	0.7	0.5	50m	100	5	10m	5*	10	B5016	Low VCE(sat)
DP021	80	75	7	2	30-130	4	0.5	0.5	3	0.1	50	4	50m	-	-	-	Low VCE(sat)
D5023	40	32	5	2	82-360	3	0.5	0.8	2	0.2	100*	5	0.5	30*	10	B5023	Low VCE(sat)
D5025	40	30	10	0.3	18k-	5	0.1	1	0.1	0.1m	200*	5	10m	3.5*	30	-	Darlington
DP053	80	80	12	0.5	10k-	5	0.1	1.5	0.1	0.1m	125	5	10m	-	-	-	Darlington
DP054	100	100	12	0.5	10k-	5	0.1	1.5	0.1	0.1m	125	5	10m	8	10	-	Darlington
D5065	50	20	7	5	230-600	2	0.5	1	3	0.1	150*	6	0.5	50	10	-	Low VCE(sat)
D5213	80	80	8	0.7	56-390	10	0.15	0.4	0.5	50m	230*	10	50m	15	10	B5213	Low VCE(sat)
D5849	50	45	5	0.5	100-600	1	0.1	0.7	0.5	50m	100	5	10m	4*	10	B5849	Very Low VCE(sat)
D5850	80	80	8	0.7	56-390	10	0.15	0.4	0.5	50m	230*	10	50m	15	10	B5850	Very Low VCE(sat)
D5858	40	25	6	1.5	85-300	1	0.1	0.5	0.8	80m	100	10	50m	4.5*	10	B5858	Low VCE(sat)
DP868	100	80	5	1	210-390	3	0.5	0.4	0.5	20m	140*	10	50m	11*	10	-	Very Low VCE(sat)
D5890	20	20	5	2	220-	2	0.5	0.21	2	0.2	100	5	0.1	35	10	B5890	Low VCE(sat)
D5905	140	120	10	1.5	2k-	5	1	1.5	1	1m	150	10	0.1	15*	10	-	Darlington
D5918	200	200 #	10	0.6	3k-	5	0.16	1.2	0.16	0.1m	60*	5	10m	5*	10	-	Darlington
D5921	80	80	7	0.5	150-	1	10m	0.25	0.1	10m	100	2	10m	-	-	-	Low VCE(sat)
DP922	100	100	5	3	10-50	4	3	1.2	3	0.375	3	10	0.5	-	-	BP922	Low VCE(sat)
D5929	50	30	9	3	360-760	2	0.5	1.1	1.5	50m	150*	6	50m	50	10	-	Low VCE(sat)
D5930	20	12	9	5	355-800	2	0.5	0.8	3	0.1	150*	6	50m	50	10	-	Low VCE(sat)
D5933	80	80	7	0.5	105-	1	10m	0.25	0.1	10m	-	-	-	-	-	-	Low VCE(sat)
D5939	50	20	9	5	230-600	2	0.5	0.8	3	0.1	150*	6	50m	50	10	-	Low VCE(sat)

Phenitec Original NPN Bipolar Transistor Characteristics Table

New = New device

*= typical, \$=VCER, #=VCES

フェニテックセミコンダクター株式会社

Chip	VCBO (V)	VCEO (V)	VEBO (V)	IC (A)	hFE (-)	VCE(sat)		VCE(sat) (V)	IC(A)	IB(A)	fT (MHz)	fT		Cob (pF)	Complement		Comment
						VCE(V)	IC(A)					VCE(V)	IE(A)		VCB(V)	Product	
D5943	40	30	10	0.3	18k-	5	0.1	1	0.1	0.1m	200*	5	10m	2*	30	B5943	Darlington
D5974	40	25	6	1.5	85-300	1	0.1	0.5	0.8	80m	100	10	50m	6.5*	10	B5974	Low VCE(sat)
D5978	25	20	12	0.5	400-2700	3	0.1	0.4	0.5	20m	250*	10	50m	7.5*	10	-	High VEBO
DP982	80	60	5	3	90-350	5	0.5	1	3	0.3	8*	5	0.5	37*	10	-	Low VCE(sat)
D5994	40	32	5	0.8	68-470	3	0.1	0.4	0.5	50m	50	5	50m	20	10	B5994	Low VCE(sat)